

# BUK7907-55ATE

TrenchPLUS standard level FET

Rev. 02 — 16 July 2002

Product data

## 1. Description

N-channel enhancement mode field-effect power transistor in a plastic package using TrenchMOS™ technology, featuring very low on state resistance, and TrenchPLUS diodes for Electrostatic Discharge (ESD) and temperature sensing.

Product availability:

BUK7907-55ATE in SOT263B.

## 2. Features

- Typical on-state resistance 5.8 mΩ
- Q101 compliant
- ESD protection
- Monolithically integrated temperature sensor for overload protection.

## 3. Applications

- Automotive and power switching:
  - ◆ 12 V and 24 V high power motor drives, e.g. Electrical Power Assisted Steering (EPAS)
  - ◆ Protected drive for lamps.

## 4. Pinning information

Table 1: Pinning - SOT263B simplified outline and symbol

Pin	Description	Simplified outline	Symbol
1	gate (g)		
2	anode (a)		
3	drain (d)		
4	cathode (k)		
5	source (s)		
mb	mounting base; connected to drain (d)		

## 5. Quick reference data

**Table 2: Quick reference data**

Symbol	Parameter	Conditions	Typ	Max	Unit
$V_{DS}$	drain-source voltage (DC)	$T_j = 25\text{ °C}$	-	55	V
$I_D$	drain current (DC)	$T_{mb} = 25\text{ °C}; V_{GS} = 10\text{ V}$	-	140	A
$P_{tot}$	total power dissipation	$T_{mb} = 25\text{ °C}$	-	272	W
$T_j$	junction temperature		-	175	°C
$R_{DSon}$	drain-source on-state resistance	$V_{GS} = 10\text{ V}; I_D = 50\text{ A}$			
		$T_j = 25\text{ °C}$	5.8	7	mΩ
		$T_j = 175\text{ °C}$	-	14	mΩ
$V_F$	temperature sense diode forward voltage	$T_j = 25\text{ °C}; I_F = 250\text{ μA}$	658	668	mV
$S_F$	temperature coefficient temperature sense diode	$-55\text{ °C} < T_j < 175\text{ °C}; I_F = 250\text{ μA}$	-1.54	-1.68	mV/K

## 6. Limiting values

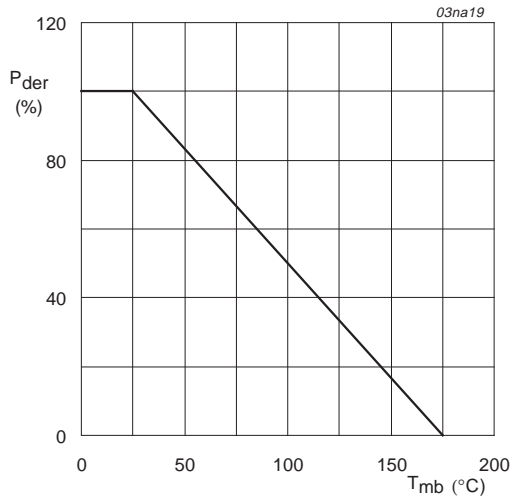
**Table 3: Limiting values**

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit	
$V_{DS}$	drain-source voltage (DC)		-	55	V	
$V_{DGS}$	drain-gate voltage (DC)		-	55	V	
$V_{GS}$	gate-source voltage (DC)		-	±20	V	
$I_D$	drain current (DC)	$T_{mb} = 25\text{ °C}; V_{GS} = 10\text{ V};$ Figure 2 and 3	[1]	-	140	A
			[2]	-	75	A
		$T_{mb} = 100\text{ °C}; V_{GS} = 10\text{ V};$ Figure 2	[2]	-	75	A
$I_{DM}$	drain current (peak value)	$T_{mb} = 25\text{ °C};$ pulsed; $t_p \leq 10\text{ }\mu\text{s};$ Figure 3	-	560	A	
$P_{tot}$	total power dissipation	$T_{mb} = 25\text{ °C};$ Figure 1	-	272	W	
$I_{GS(CL)}$	gate-source clamp current	continuous	-	10	mA	
		$t_p = 5\text{ ms}; \delta = 0.01$	-	50	mA	
$V_{isol(FET-TSD)}$	FET to temperature sense diode isolation voltage		-	±100	V	
$T_{stg}$	storage temperature		-55	+175	°C	
$T_j$	junction temperature		-55	+175	°C	
<b>Source-drain diode</b>						
$I_{DR}$	reverse drain current	$T_{mb} = 25\text{ °C}$	[1]	-	140	A
			[2]	-	75	A
$I_{DRM}$	pulsed reverse drain current	$T_{mb} = 25\text{ °C};$ pulsed; $t_p \leq 10\text{ }\mu\text{s}$	-	560	A	
<b>Avalanche ruggedness</b>						
$E_{DS(AL)S}$	non-repetitive avalanche energy	unclamped inductive load; $I_D = 68\text{ A};$ $V_{DS} \leq 55\text{ V}; V_{GS} = 10\text{ V}; R_{GS} = 50\text{ }\Omega;$ starting $T_j = 25\text{ °C}$	-	460	mJ	
<b>Electrostatic Discharge</b>						
$V_{esd}$	electrostatic discharge voltage; pins 1,3,5	human body model; $C = 100\text{ pF};$ $R = 1.5\text{ k}\Omega$		6	kV	

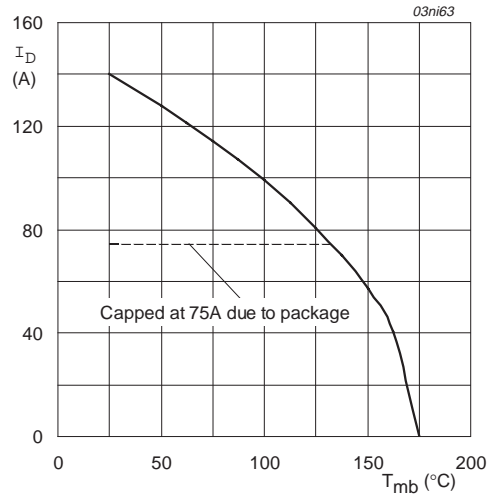
[1] Current is limited by power dissipation chip rating.

[2] Continuous current is limited by package.



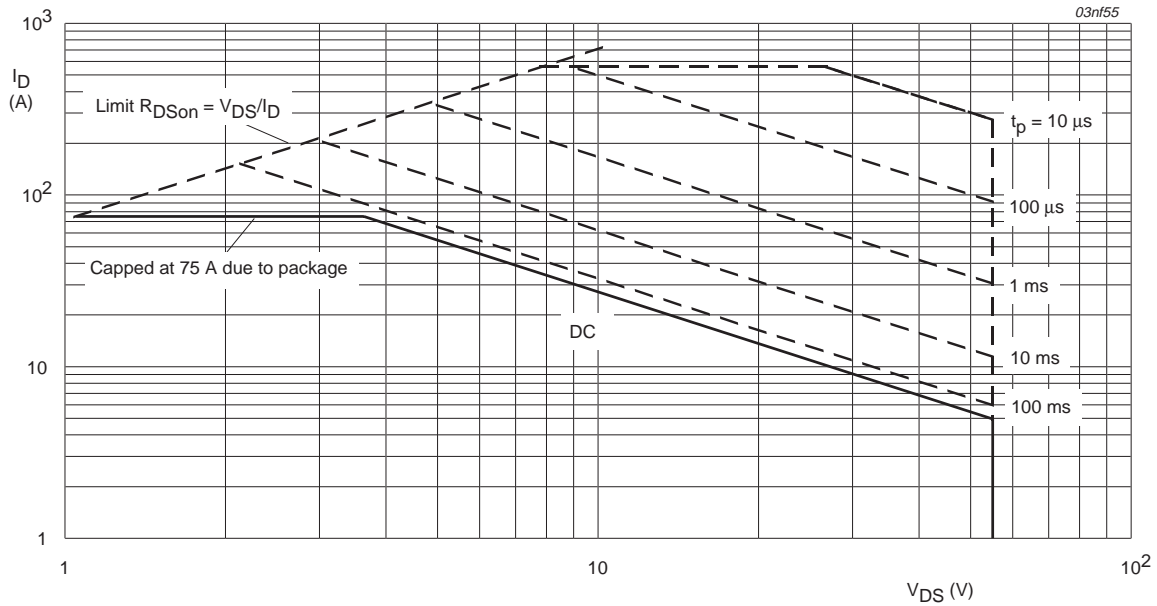
$$P_{der} = \frac{P_{tot}}{P_{tot(25^{\circ}C)}} \times 100\%$$

**Fig 1. Normalized total power dissipation as a function of mounting base temperature.**



$V_{GS} \geq 10\text{ V}$

**Fig 2. Continuous drain current as a function of mounting base temperature.**



$T_{mb} = 25^{\circ}C$ ;  $I_{DM}$  single pulse.

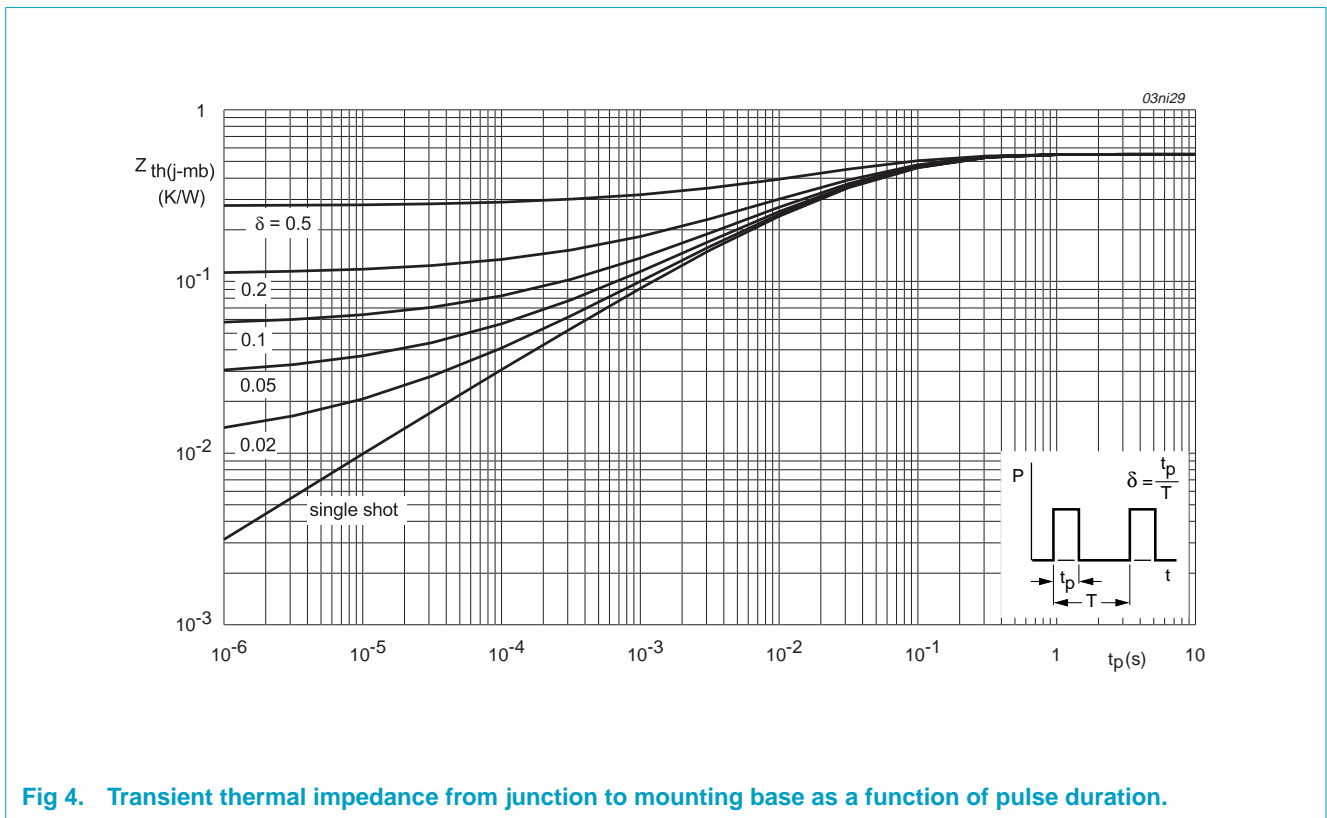
**Fig 3. Safe operating area; continuous and peak drain currents as a function of drain-source voltage.**

## 7. Thermal characteristics

**Table 4: Thermal characteristics**

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$R_{th(j-a)}$	thermal resistance from junction to ambient	vertical in still air	-	60	-	K/W
$R_{th(j-mb)}$	thermal resistance from junction to mounting base	Figure 4	-	-	0.55	K/W

### 7.1 Transient thermal impedance



**Fig 4. Transient thermal impedance from junction to mounting base as a function of pulse duration.**

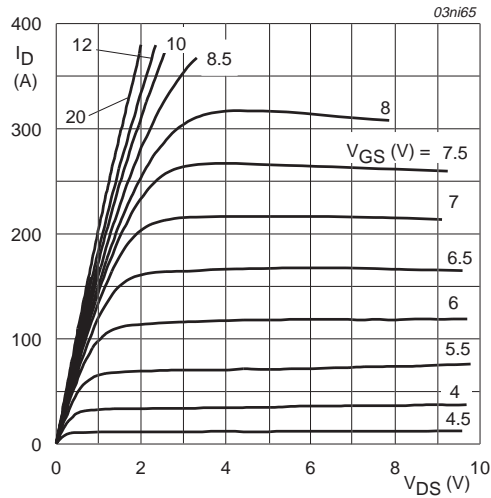
## 8. Characteristics

**Table 5: Characteristics**
 $T_j = 25\text{ °C}$  unless otherwise specified.

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
<b>Static characteristics</b>						
$V_{(BR)DSS}$	drain-source breakdown voltage	$I_D = 0.25\text{ mA}; V_{GS} = 0\text{ V}$				
		$T_j = 25\text{ °C}$	55	-	-	V
		$T_j = -55\text{ °C}$	50	-	-	V
$V_{GS(th)}$	gate-source threshold voltage	$I_D = 1\text{ mA}; V_{DS} = V_{GS};$ <b>Figure 9</b>				
		$T_j = 25\text{ °C}$	2	3	4	V
		$T_j = 175\text{ °C}$	1	-	-	V
		$T_j = -55\text{ °C}$	-	-	4.4	V
$I_{DSS}$	drain-source leakage current	$V_{DS} = 55\text{ V}; V_{GS} = 0\text{ V}$				
		$T_j = 25\text{ °C}$	-	0.1	10	$\mu\text{A}$
		$T_j = 175\text{ °C}$	-	-	250	$\mu\text{A}$
$V_{(BR)GSS}$	gate-source breakdown voltage	$I_G = \pm 1\text{ mA};$ $-55\text{ °C} < T_j < 175\text{ °C}$	20	22	-	V
$I_{GSS}$	gate-source leakage current	$V_{GS} = \pm 10\text{ V}; V_{DS} = 0\text{ V}$				
		$T_j = 25\text{ °C}$	-	22	1000	nA
		$T_j = 175\text{ °C}$	-	-	10	$\mu\text{A}$
$R_{DS(on)}$	drain-source on-state resistance	$V_{GS} = 10\text{ V}; I_D = 50\text{ A};$ <b>Figure 7 and 8</b>				
		$T_j = 25\text{ °C}$	-	5.8	7	m $\Omega$
		$T_j = 175\text{ °C}$	-	-	14	m $\Omega$
$V_F$	forward voltage, temperature sense diode	$I_F = 250\text{ }\mu\text{A}$	648	658	668	mV
$S_F$	temperature coefficient temperature sense diode	$I_F = 250\text{ }\mu\text{A};$ $-55\text{ °C} < T_j < 175\text{ °C}$	-1.4	-1.54	-1.68	mV/K
$V_{hys}$	temperature sense diode forward voltage hysteresis	$125\text{ }\mu\text{A} < I_F < 250\text{ }\mu\text{A}$	25	32	50	mV
<b>Dynamic characteristics</b>						
$Q_{g(tot)}$	total gate charge	$V_{GS} = 10\text{ V}; V_{DS} = 25\text{ V};$ $I_D = 25\text{ A};$ <b>Figure 14</b>	-	116	-	nC
$Q_{gs}$	gate-source charge		-	19	-	nC
$Q_{gd}$	gate-to-drain (Miller) charge		-	50	-	nC
$C_{iss}$	input capacitance	$V_{GS} = 0\text{ V}; V_{DS} = 25\text{ V};$ $f = 1\text{ MHz};$ <b>Figure 12</b>	-	4500	-	pF
$C_{oss}$	output capacitance		-	960	-	pF
$C_{rss}$	reverse transfer capacitance		-	510	-	pF
$t_{d(on)}$	turn-on delay time	$V_{DD} = 30\text{ V}; R_L = 1.2\text{ }\Omega;$ $V_{GS} = 10\text{ V}; R_G = 10\text{ }\Omega$	-	36	-	ns
$t_r$	rise time		-	115	-	ns
$t_{d(off)}$	turn-off delay time		-	159	-	ns
$t_f$	fall time		-	111	-	ns

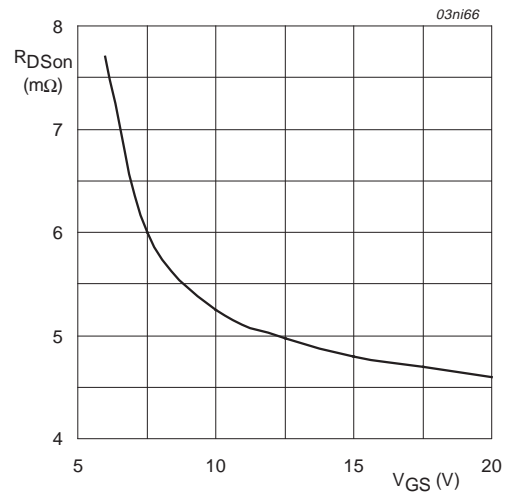
**Table 5: Characteristics...***continued**T<sub>j</sub> = 25 °C unless otherwise specified.*

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
L <sub>d</sub>	internal drain inductance	from upper edge of drain mounting base to center of die	-	2.5	-	nH
L <sub>s</sub>	internal source inductance	from source lead to source bond pad	-	7.5	-	nH
<b>Source-drain diode</b>						
V <sub>SD</sub>	source-drain (diode forward) voltage	I <sub>S</sub> = 25 A; V <sub>GS</sub> = 0 V; Figure 17	-	0.85	1.2	V
t <sub>rr</sub>	reverse recovery time	I <sub>S</sub> = 20 A; dI <sub>S</sub> /dt = -100 A/μs	-	80	-	ns
Q <sub>r</sub>	recovered charge	V <sub>GS</sub> = -10 V; V <sub>DS</sub> = 30 V	-	200	-	nC



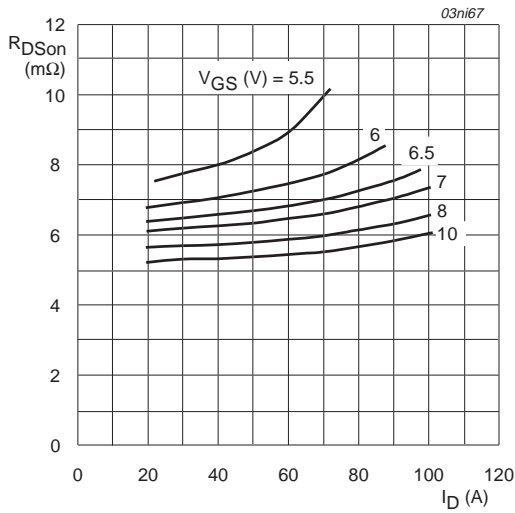
$T_j = 25\text{ }^\circ\text{C}$ ;  $t_p = 300\text{ }\mu\text{s}$

**Fig 5. Output characteristics: drain current as a function of drain-source voltage; typical values.**



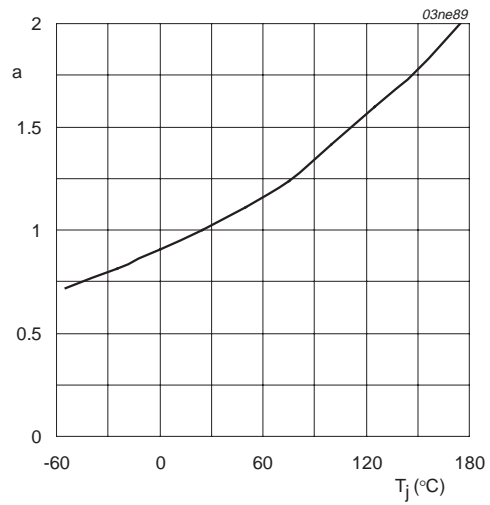
$T_j = 25\text{ }^\circ\text{C}$ ;  $I_D = 50\text{ A}$

**Fig 6. Drain-source on-state resistance as a function of gate-source voltage; typical values.**



$T_j = 25\text{ }^\circ\text{C}$ ;  $t_p = 300\mu\text{s}$

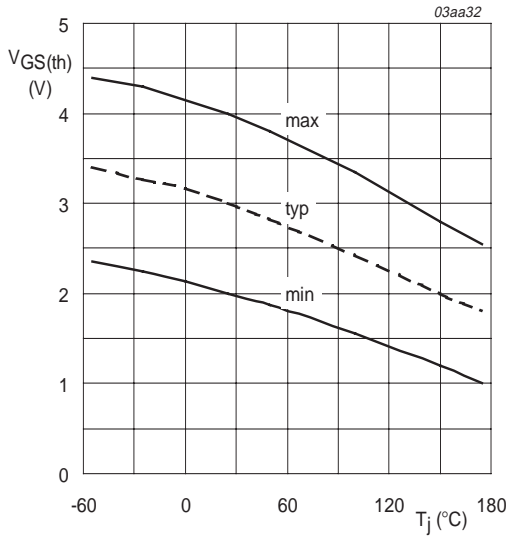
**Fig 7. Drain-source on-state resistance as a function of drain current; typical values.**



$$a = \frac{R_{DSon}}{R_{DSon(25^\circ\text{C})}}$$

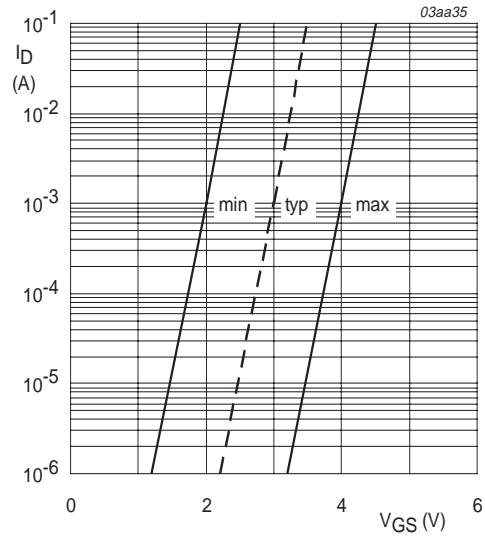
**Fig 8. Normalized drain-source on-state resistance factor as a function of junction temperature.**





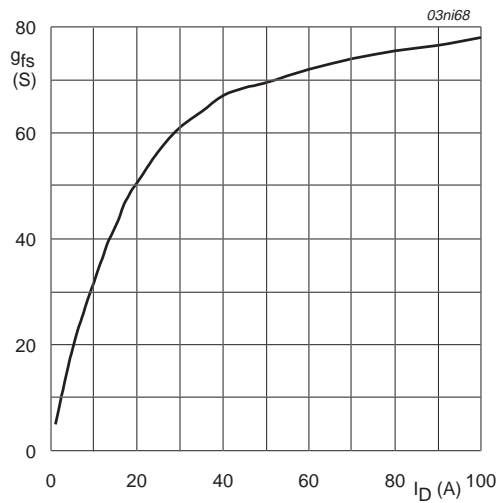
$I_D = 1 \text{ mA}; V_{DS} = V_{GS}$

**Fig 9. Gate-source threshold voltage as a function of junction temperature.**



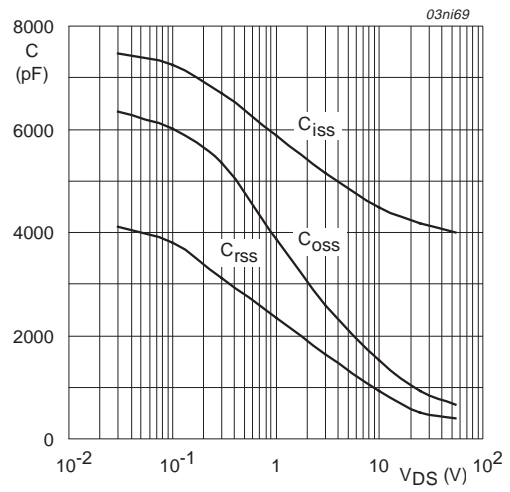
$T_j = 25 \text{ }^{\circ}C; V_{DS} = V_{GS}$

**Fig 10. Sub-threshold drain current as a function of gate-source voltage.**



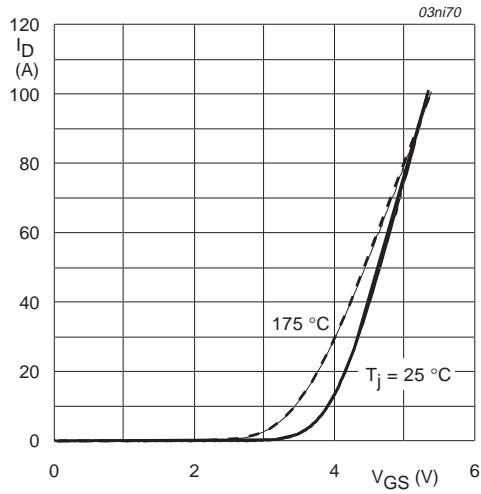
$T_j = 25 \text{ }^{\circ}C; V_{DS} = 25 \text{ V}$

**Fig 11. Forward transconductance as a function of drain current; typical values.**



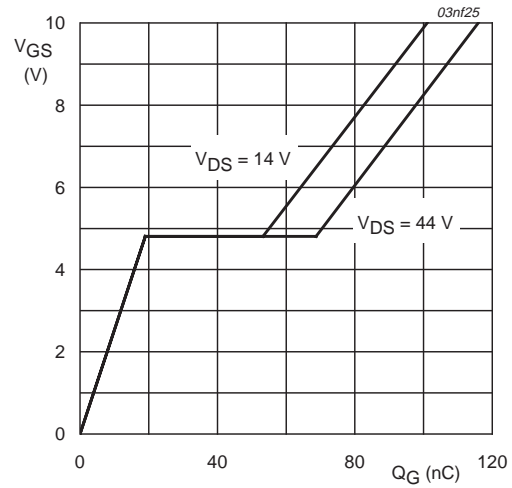
$V_{GS} = 0 \text{ V}; f = 1 \text{ MHz}$

**Fig 12. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values.**



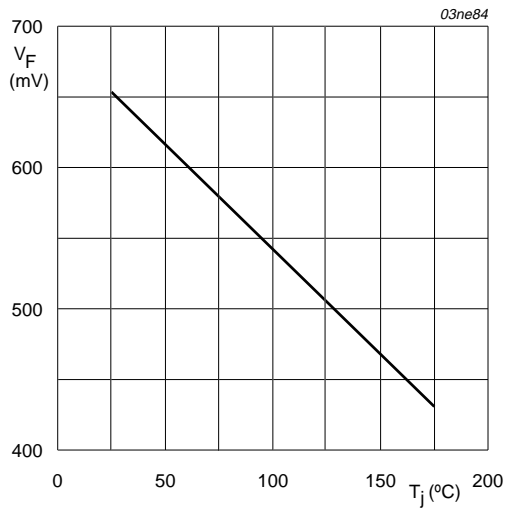
$V_{DS} = 25$  V

**Fig 13. Transfer characteristics: drain current as a function of gate-source voltage; typical values.**



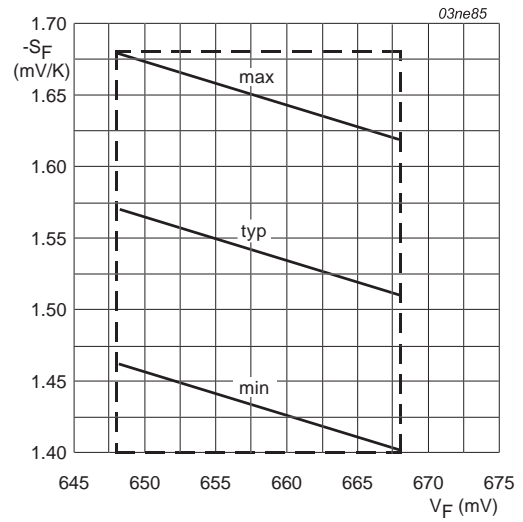
$T_j = 25$  °C;  $I_D = 25$  A

**Fig 14. Gate-source voltage as a function of turn-on gate charge; typical values.**



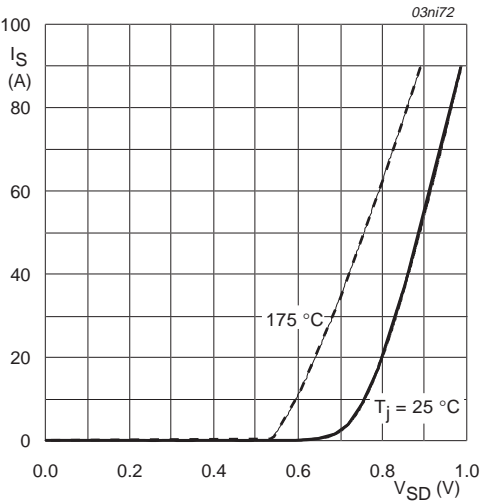
$I_F = 250$   $\mu$ A

**Fig 15. Forward voltage of temperature sense diode as a function of junction temperature; typical values.**



$V_F$  at  $T_j = 25$  °C;  $I_F = 250$   $\mu$ A

**Fig 16. Temperature coefficient of temperature sense diode as a function of forward voltage; typical values.**



$V_{GS} = 0\text{ V}$

Fig 17. Reverse diode current as a function of reverse diode voltage; typical values.

**9. Package outline**

Plastic single-ended package; heatsink mounted; 1 mounting hole; 5-lead TO-220

SOT263B

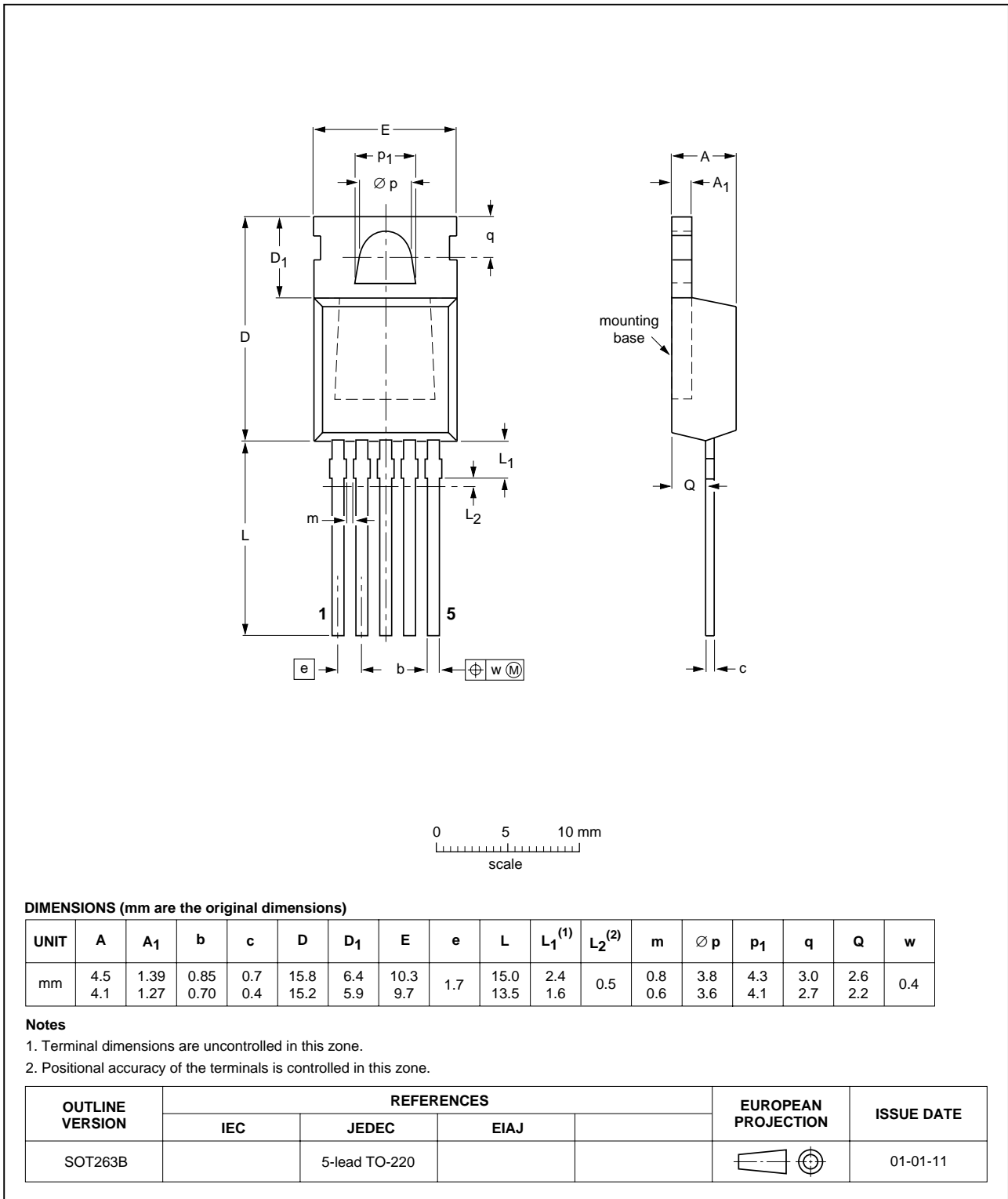


Fig 18. SOT263B.

## 10. Revision history

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Table 6: Revision history

Rev	Date	CPCN	Description
02	20020716	-	Product data; second version; supersedes initial version of 20020124
01	20020124	-	Product data; initial version

## 11. Data sheet status

Data sheet status <sup>[1]</sup>	Product status <sup>[2]</sup>	Definition
Objective data	Development	This data sheet contains data from the objective specification for product development. Philips Semiconductors reserves the right to change the specification in any manner without notice.
Preliminary data	Qualification	This data sheet contains data from the preliminary specification. Supplementary data will be published at a later date. Philips Semiconductors reserves the right to change the specification without notice, in order to improve the design and supply the best possible product.
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[1] Please consult the most recently issued data sheet before initiating or completing a design.

[2] The product status of the device(s) described in this data sheet may have changed since this data sheet was published. The latest information is available on the Internet at URL <http://www.semiconductors.philips.com>.

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**Limiting values definition** — Limiting values given are in accordance with the Absolute Maximum Rating System (IEC 60134). Stress above one or more of the limiting values may cause permanent damage to the device. These are stress ratings only and operation of the device at these or at any other conditions above those given in the Characteristics sections of the specification is not implied. Exposure to limiting values for extended periods may affect device reliability.

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**Contents**

1 **Description** . . . . . 1

2 **Features** . . . . . 1

3 **Applications** . . . . . 1

4 **Pinning information** . . . . . 1

5 **Quick reference data** . . . . . 2

6 **Limiting values** . . . . . 3

7 **Thermal characteristics** . . . . . 5

7.1 Transient thermal impedance . . . . . 5

8 **Characteristics** . . . . . 6

9 **Package outline** . . . . . 12

10 **Revision history** . . . . . 13

11 **Data sheet status** . . . . . 14

12 **Definitions** . . . . . 14

13 **Disclaimers** . . . . . 14

14 **Trademarks** . . . . . 14



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